

L Number	Hits	Search Text	DB	Time stamp
1	738	(438/652).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 10:10
2	232	438/652.ccls. and barrier and ((atomic adj layer deposit\$6) or ("ALD"))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 10:11
3	1	("20040115929").PN.	US-PGPUB	2004/10/18 09:02
4	2172	(438/586).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 10:11
5	276	(438/658).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 10:11
6	953	(438/653).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 10:11
7	1261	(438/643).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 10:11
8	652	(438/683).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 10:11
9	2089	438/652,653,658,643,683,586.ccls. and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and @ad<20031210	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 10:12
10	1876	438/652,653,658,643,683,586.ccls. and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and @ad<20031210	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 10:14
11	378	(438/652,653,658,643,683,586.ccls. and (hole or open\$6 or aperture or groove or trench or via) and barrier and ((atomic adj layer deposit\$6) or ("ALD")) and @ad<20031210) and repe\$9	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 10:14
-	1078	semiconductor and ((insulat\$ or dielectric or oxide) adj (layer or film)) and (hole or aperture or via or trench or open\$4) and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and @ad<=20031210	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 11:33
-	745	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) same (hole or aperture or via or trench or open\$4)) and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and @ad<=20031210	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/10/18 08:33
-	595	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) with (hole or aperture or via or trench or open\$4)) and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and @ad<=20031210	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 11:32

-	457	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) with (hole or aperture or via or trench or open\$4)) and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and (barrier or (diffus\$6 adj prevent\$6)) and @ad<=20031210	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 11:33
-	552	semiconductor and (((insulat\$ or dielectric or oxide) adj (layer or film)) same (hole or aperture or via or trench or open\$4)) and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and (barrier or (diffus\$6 adj prevent\$6)) and @ad<=20031210	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 11:33
-	752	semiconductor and ((insulat\$ or dielectric or oxide) adj (layer or film)) and (hole or aperture or via or trench or open\$4) and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and (barrier or (diffus\$6 adj prevent\$6)) and @ad<=20031210	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 11:33
-	222	semiconductor and (insulat\$ adj layer) and hole and ((atomic adj layer adj deposit\$6) or ("ALD")) and (repeat\$8 or times) and (barrier) and @ad<=20031210	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 12:00
-	22254	lim.inv.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 11:58
-	173	lim.inv. and bio	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 12:04
-	3	lim.inv. and bi and (atomic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 12:05
-	239	lim.inv. and bi and o	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 12:05
-	1	(lim.inv. and bi and o) and (atomic adj layer)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2004/09/01 12:05